



AMP4032 SOLID STATE HIGH POWER AMPLIFIER

FEATURES

- Class AB linear GaAsFET design
- Instantaneous wide bandwidth
- Designed for EMI/RFI, lab, and general communication applications
- Suitable for all single channel modulation standards
- Rack mounted system
- Local LCD & remote flexible interfaces
- High reliability and ruggedness



ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	18 - 26.5 GHz	
Power Output CW	10 Watt Typical	Few frequency spots that could be marginal 10W.
Power Output @ P1dB	6 Watt Typ	
Power Gain	40 dB Min	
Power Gain Flatness	4.0 dB p-p Max	Constant input power
Input Return Loss	-10 dB Max	Relative to 50 Ohm
2-Tone Intermodulation (IMD)	-30 dBc Typ	30dBm/Tone, $\Delta = 1\text{MHz}$
Harmonics	-20 dBc Typ	At rated Pout
Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	100 - 240 VAC	
Power Consumption	220 Watt Max	
Input Power Protection	+3 dBm Max	10 Sec without damage
Load VSWR Protection	5 : 1	<1 minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Ambient Temperature	0 to +50 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions W x H x D	430 x 88 x 562 mm	2U
Weight	9 kg.	
RF Connectors In/Out	2.9 mm (K / air type) Female	
AC Power / Interface Connector	IEC 60320-C14 / 9-Pin D-Sub	
Cooling	Built in Fan Cooling	
OPTIONAL: Digital Monitor & Control FWD, REV, VSWR, GAIN, ALC, V & I, TEMP	Ethernet RJ-45 TCP/IP, RS422/485 Optional GPIB Interface	Remote Bluetooth application

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OUTLINE DRAWING

